

METHOD FOR ULTRA-THIN FILM FORMATION

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ABSTRACT OF THE DISCLOSURE

- 5 A method for forming a thin film on a semiconductor wafer. The method includes loading a semiconductor wafer into a process chamber while the process chamber is under vacuum pressure, or alternatively, while the partial pressure of the reactive gas is substantially zero. The process gas is introduced under pressure into the process chamber. The semiconductor wafer is unloaded from the process
- 10 chamber while the process chamber is under a vacuum pressure, or alternatively while the partial pressure of the reactive gas is substantially zero.